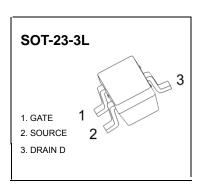


## JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

# **SOT-23-3L Plastic-Encapsulate MOSFETS**

# CJK3400A N-Channel Enhancement Mode Field Effect Transistor

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> MAX	I <sub>D</sub>
	32mΩ@10V	
30 V	38mΩ@4.5V	5.8A
	45mΩ@2.5V	



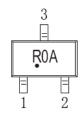
#### **FEATURE**

- High dense cell design for extremely low R<sub>DS(ON)</sub>
- Exceptional on-resistance and maximum DC current capability •

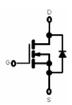
#### **APPLICATION**

- Load/Power Switching
- Interfacing Switching

#### **MARKING**



# **Equivalent Circuit**



Solid dot = Green molding compound device, if none,the normal device.

### Maximum ratings ( T<sub>a</sub>=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	$V_{GS}$	±12	V
Continuous Drain Current	I <sub>D</sub>	5.8	Α
Drain Current-Pulsed (note 1)	I <sub>DM</sub>	30	Α
Power Dissipation	$P_D$	450	mW
Thermal Resistance from Junction to Ambient (note 2)	$R_{\theta JA}$	313	°C/W
Junction Temperature	$T_J$	150	℃
Storage Temperature	T <sub>STG</sub>	-55~+150	$^{\circ}$

## **MOSFET ELECTRICAL CHARACTERISTICS**

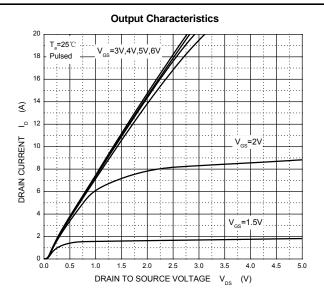
## T<sub>a</sub>=25 ℃ unless otherwise specified

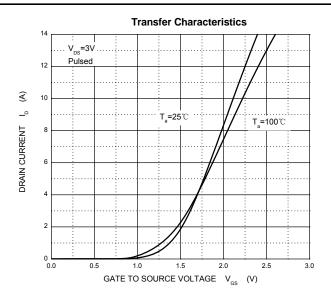
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	V(BR) DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	30			V
Zero gate voltage drain current	Ipss	V <sub>DS</sub> =24V,V <sub>GS</sub> = 0V			1	μΑ
Gate-source leakage current	Igss	V <sub>GS</sub> =±12V, V <sub>DS</sub> = 0V			±100	nA
On characteristics (note 3)			•	•		
Paris and a second seco		V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A		29	32	mΩ
Drain-source on-resistance	RDS(on)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5A		32	38	mΩ
		V <sub>GS</sub> =2.5V,I <sub>D</sub> =4A		40	45	mΩ
Forward tranconductance	<b>g</b> FS	V <sub>DS</sub> =5V, I <sub>D</sub> =5A	8			S
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.7	0.9	1.4	V
Dynamic Characteristics (note	4,5)					
Input capacitance	Ciss				1155	pF
Output capacitance	Coss	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,f =1MHz		108		pF
Reverse transfer capacitance	Crss			84		pF
Gate resistance	Rg	V <sub>DS</sub> =0V,V <sub>GS</sub> =0V,f =1MHz			3.6	Ω
Switching Characteristics (note	e 4,5)		•	•		
Turn-on delay time	<b>t</b> d(on)				5	ns
Turn-on rise time	tr	V <sub>GS</sub> =10V,V <sub>DS</sub> =15V,			7	ns
Turn-off delay time	td(off)	$R_L$ =2.7 $\Omega$ , $R_{GEN}$ =3 $\Omega$			40	ns
Turn-off fall time	<b>t</b> f	]			6	ns
Drain-source diode characterist	ics and maxi	mum ratings	•		•	•
Diode forward voltage (note 3)	$V_{SD}$	I <sub>S</sub> =1A,V <sub>GS</sub> =0V			1	V

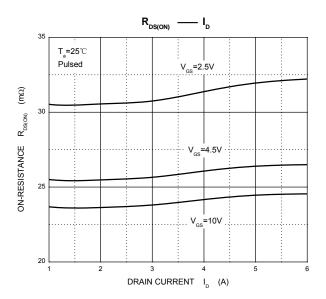
### Note:

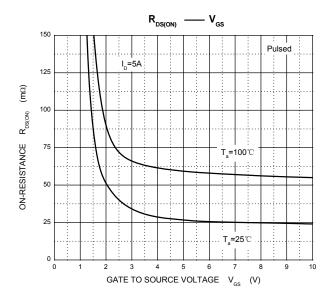
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t < 5 sec.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.

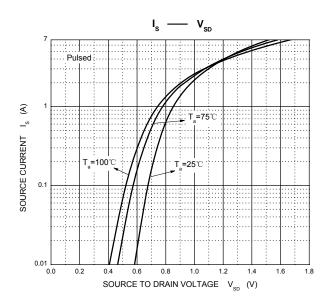
## **Typical Characteristics**

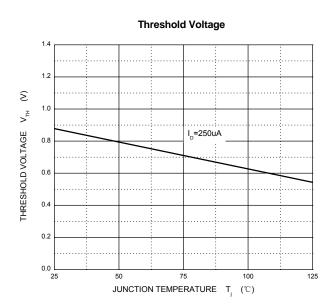




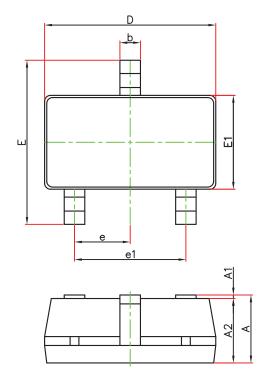


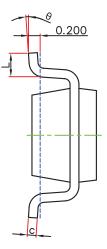






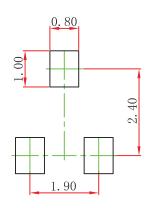
## **SOT-23-3L Package Outline Dimensions**





Symbol	Dimensions In	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E1	1.500	1.700	0.059	0.067	
E	2.650	2.950	0.104	0.116	
е	0.950(	BSC)	0.037	(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

# **SOT-23-3L Suggested Pad Layout**



#### Note:

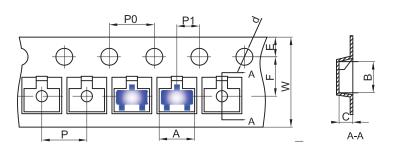
- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

#### NOTICE

JCET reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JCET does not assume any liability arising out of the application or use of any product described herein.

## SOT-23-3L Tape and Reel

## SOT-23-3L Embossed Carrier Tape

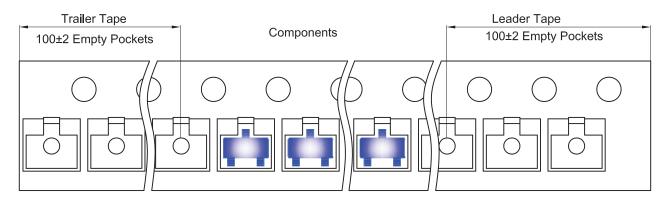


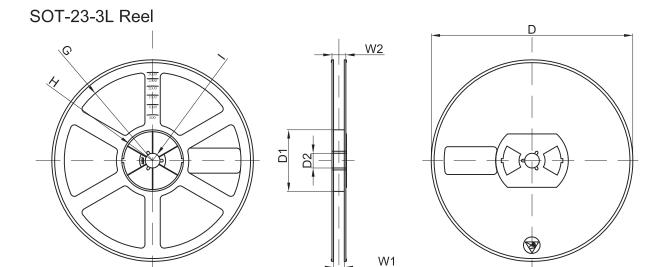
#### Packaging Description:

SOT-23-3L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type A B C d E F P0 P P1 W										
SOT-23-3L	3.18	3.28	1.32	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

## SOT-23-3L Tape Leader and Trailer





Dimensions are in millimeter									
Reel Option	D	D1	D2	G	Н	I	W1	W2	
7"Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10	

REEL	Reel Size	Вох	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	